

SOIC-16 WB D SUFFIX CASE 751G

PIN CONNECTIONS

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Maximum Operating Voltage	V _{CC}	24	V _{DC}
Operating Ambient Temperature Range	T _A	0 to +70	°C
Operating Junction Temperature	TJ	150	°C
Power Dissipation	PD	400	mW
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	105	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 9 of this data sheet.



Figure 1. Block Diagram

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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CIRCUIT DESCRIPTION

The NE570 compandor building blocks, as shown in the block diagram, are a full–wave rectifier, a variable gain cell, an operational amplifier and a bias system. The arrangement of these blocks in the IC result in a circuit which can perform well with few external components, yet can be adapted to many diverse applications.

The full–wave rectifier rectifies the input current which flows from the rectifier input, to an internal summing node which is biased at V_{REF} . The rectified current is averaged on an external filter capacitor tied to the C_{RECT} terminal, and the average value of the input current controls the gain of the variable gain cell. The gain will thus be proportional to the average value of the input signal for capacitively–coupled voltage inputs as shown in the following equation. Note that for capacitively–coupled inputs there is no offset voltage capable of producing a gain error. The only error will come from the bias current of the rectifier (supplied internally) which is less than 0.1 μ A.

or

$$G \propto \frac{|V_{IN}| avg}{R_1}$$

 $G \propto \frac{|V_{IN} - V_{REF}| \text{ avg}}{R_1}$

The speed with which gain changes to follow changes in input signal levels is determined by the rectifier filter capacitor. A small capacitor will yield rapid response but will not fully filter low frequency signals. Any ripple on the gain control signal will modulate the signal passing through the variable gain cell. In an expander or compressor application, this would lead to third harmonic distortion, so there is a trade–off to be made between fast attack and decay times and distortion. For step changes in amplitude, the





BASIC CIRCUIT HOOK-UP AND OPERATION

Figure 5 shows the block diagram of one half of the chip, (there are two identical channels on the IC). The full–wave averaging rectifier provides a gain control current, I_G, for the variable gain (Δ G) cell. The output of the Δ G cell is a current which is fed to the summing node of the operational amplifier. Resistors are provided to establish circuit gain and set the output DC bias.

CIRCUIT DETAILS-RECTIFIER

Figure 8 shows the concept behind the full–wave averaging rectifier. The input current to the summing node of the op amp, V_{IN}/R_1 , is supplied by the output of the op amp. If we can mirror the op amp output current into a unipolar current, we will have an ideal rectifier. The output current is averaged by R_5 , C_R , which set the averaging time constant, and then mirrored with a gain of 2 to become I_G , the gain control current.

Figure 9 shows the rectifier circuit in more detail. The op amp is a one-stage op amp, biased so that only one output device is on at a time. The non-inverting input, (the base of Q_1), which is shown grounded, is actually tied to the internal 1.8 V V_{REF}. The inverting input is tied to the op amp output, (the emitters of Q_5 and Q_6), and the input summing resistor

NE570

At very high frequencies, the response of the rectifier will fall off. The roll–off will be more pronounced at lower input levels due to the increasing amount of gain required to switch between Q_5 or Q_6 conducting. The rectifier frequency response for input levels of 0 dBm, –20 dBm, and –40 dBm is shown in Figure 11. The response at all three levels is flat to well above the audio range.



Figure 11. Rectifier Frequency Response vs. Input Level

VARIABLE GAIN CELL

Figure 12 is a diagram of the variable gain cell. This is a linearized two–quadrant transconductance multiplier. Q_1 , Q_2 and the op amp provide a predistorted drive signal for the gain control pair, Q_3 and Q_4 . The gain is controlled by I_G and a current mirror provides the output current.



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-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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